ALPHA & OMEGA SEMICONDUCTOR

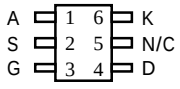
AO6701
P-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

General Description

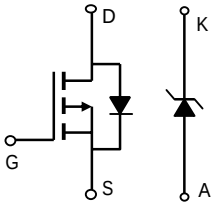
The AO6701 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. *Standard Product AO6701 is Pb-free (meets ROHS & Sony 259 specifications). AO6701L is a Green Product ordering option. AO6701 and AO6701L are electrically identical.*

Features

V_{DS} (V) = -30V
I_D = -2.3A (V_{GS} = -10V)
$R_{DS(ON)}$ < 135mΩ (V_{GS} = -10V)
$R_{DS(ON)}$ < 185mΩ (V_{GS} = -4.5V)
$R_{DS(ON)}$ < 265mΩ (V_{GS} = -2.5V)
SCHOTTKY
V_{DS} (V) = 20V, I_F = 1A, V_F<0.5V@0.5A



TSOP6



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	MOSFET	Schottky	Units
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	±12		V
Continuous Drain Current [A]	T_A=25°C	I_D	-2.3		A
	T_A=70°C		-1.8		
Pulsed Drain Current [B]		I_{DM}	-15		
Schottky reverse voltage		V_{KA}		20	V
Continuous Forward Current [A]	T_A=25°C	I_F		2	A
	T_A=70°C			1	
Pulsed Forward Current [B]		I_{FM}		10	
Power Dissipation	T_A=25°C	P_D	1.15	0.92	W
	T_A=70°C		0.7	0.59	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	-55 to 150	°C

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	78	110	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		106	150	
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	64	80	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	109.4	135	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		136.5	175	
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	58.5	80	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-0.6	-1	-1.4	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-2.3A		107	135	mΩ
		T_J=125°C		154	190	
		V_{GS}=-4.5V, I_D=-2A		135	185	mΩ
		V_{GS}=-2.5V, I_D=-1A		195	265	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-2.3A		8		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.85	-1	V
I_S	Maximum Body-Diode Continuous Current				-1.35	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		409		pF
C_{oss}	Output Capacitance			55		pF
C_{rss}	Reverse Transfer Capacitance			42		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-15V, I_D=-2.0A		4.9		nC
Q_{gs}	Gate Source Charge			0.6		nC
Q_{gd}	Gate Drain Charge			1.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=7.5Ω, R_{GEN}=3Ω		6.9		ns
t_r	Turn-On Rise Time			3.3		ns
$t_{D(off)}$	Turn-Off DelayTime			38.5		ns
t_f	Turn-Off Fall Time			13.2		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-2.0A, dI/dt=100A/µs		15		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-2.0A, dI/dt=100A/µs		8		nC
SCHOTTKY PARAMETERS						
V_F	Forward Voltage Drop	I_F=0.5A		0.39	0.5	V
I_{rm}	Maximum reverse leakage current	V_R=16V			0.1	mA
		V_R=16V, T_J=125°C			20	
C_T	Junction Capacitance	V_R=10V		34		pF
t_{rr}	SchottkyReverse Recovery Time	I_F=1A, dI/dt=100A/µs		5.2	10	ns
Q_{rr}	Schottky Reverse Recovery Charge	I_F=1A, dI/dt=100A/µs		0.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev2: August 2005

MOSFET TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

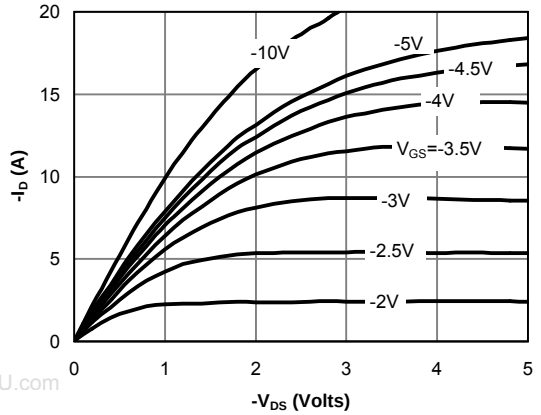


Fig 1: On-Region Characteristics

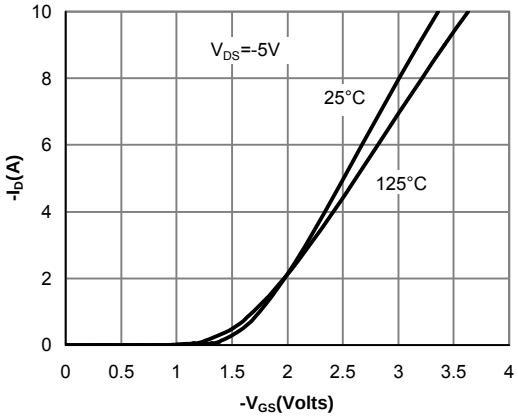


Figure 2: Transfer Characteristics

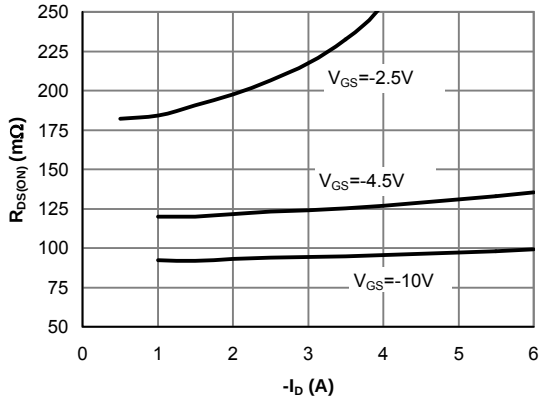


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

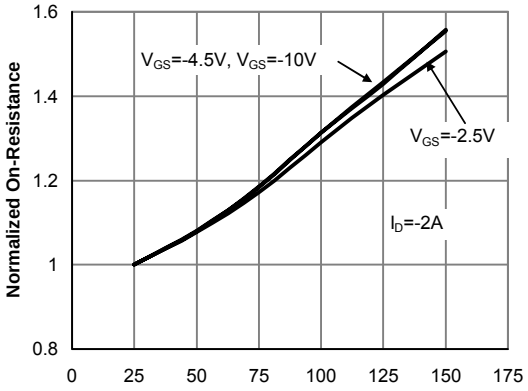


Figure 4: On-Resistance vs. Junction Temperature

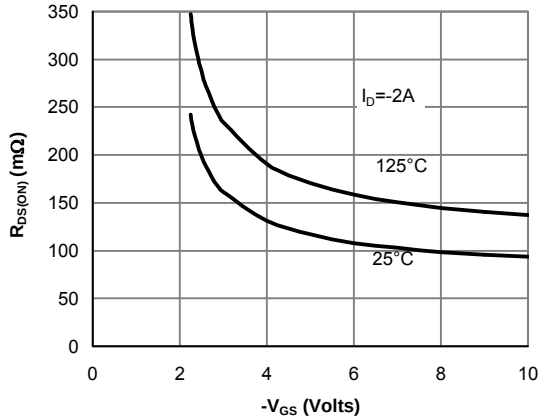


Figure 5: On-Resistance vs. Gate-Source Voltage

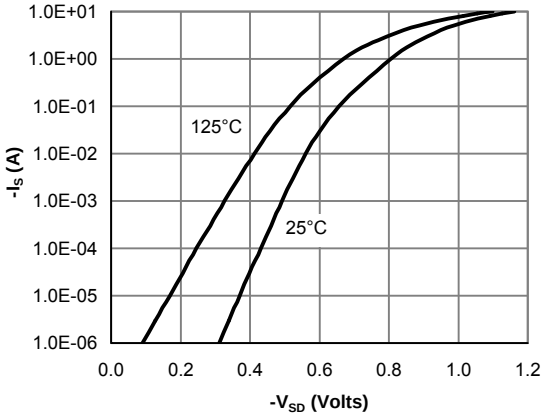


Figure 6: Body-Diode Characteristics

MOSFET TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

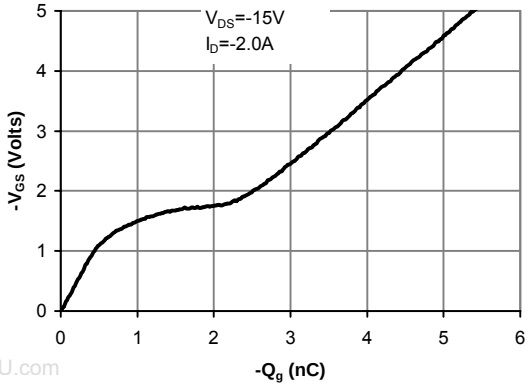


Figure 7: Gate-Charge Characteristics

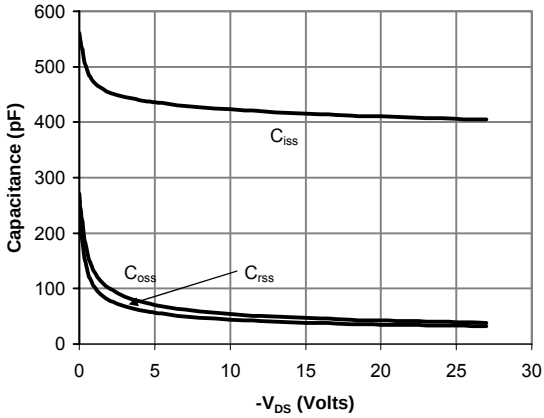


Figure 8: Capacitance Characteristics

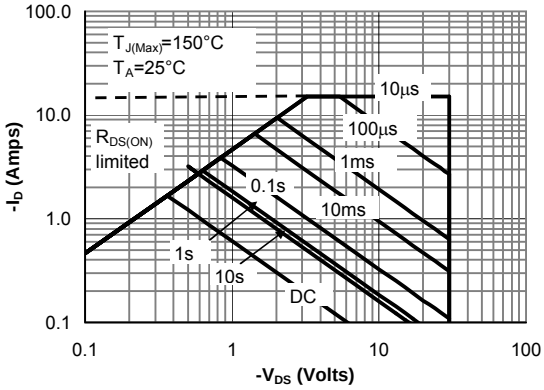


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

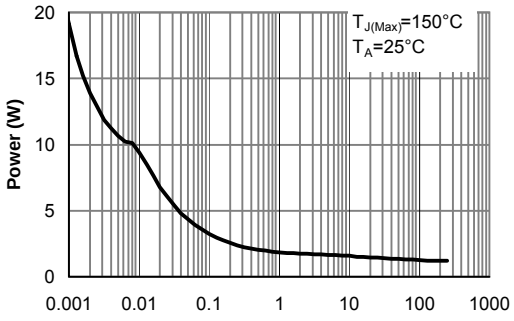


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

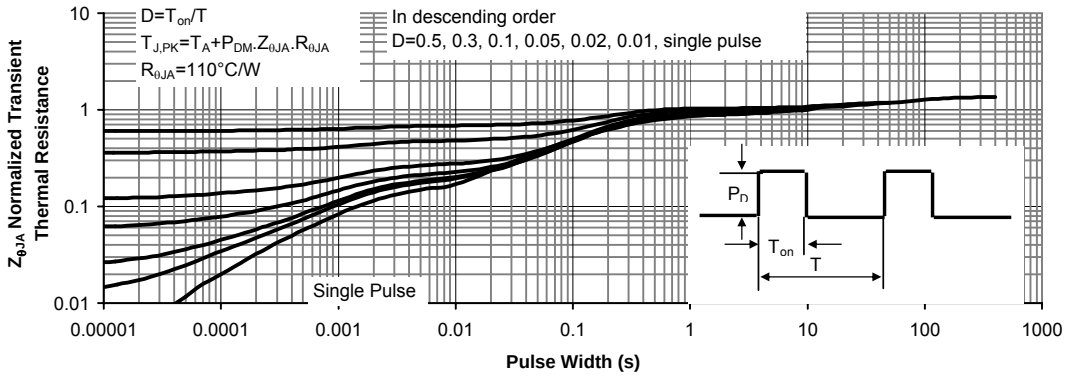


Figure 11: Normalized Maximum Transient Thermal Impedance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

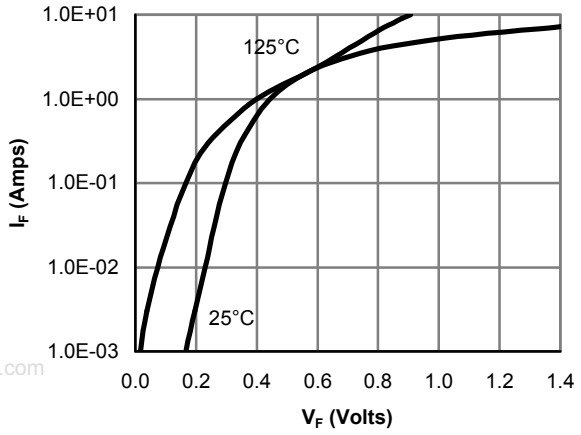


Figure 12: Schottky Forward Characteristics

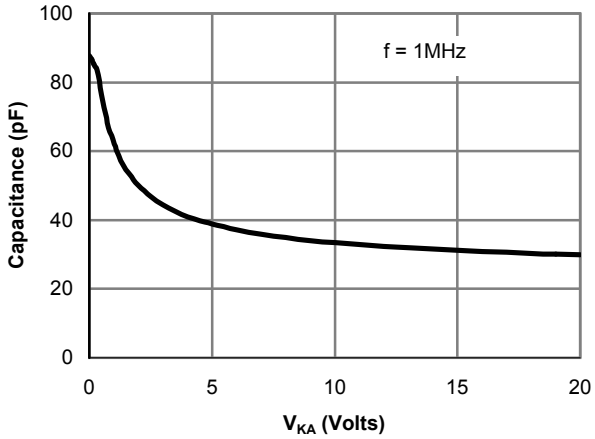


Figure 13: Schottky Capacitance Characteristics

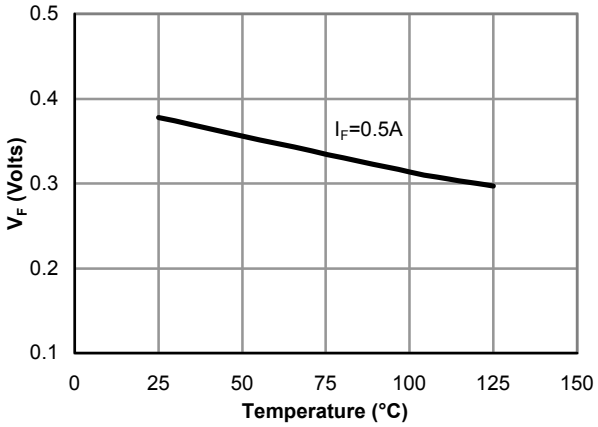


Figure 14: Schottky Forward Drop vs. Junction Temperature

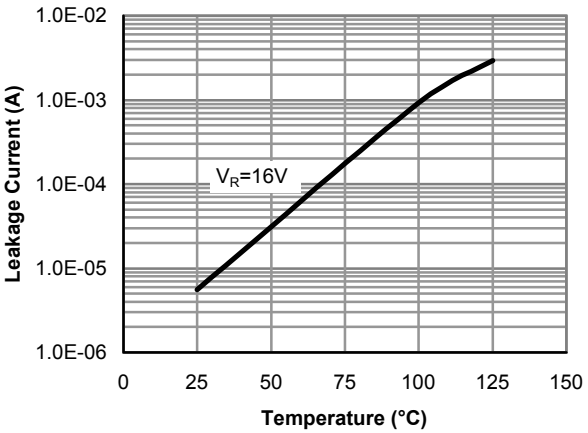


Figure 15: Schottky Leakage current vs. Junction Temperature

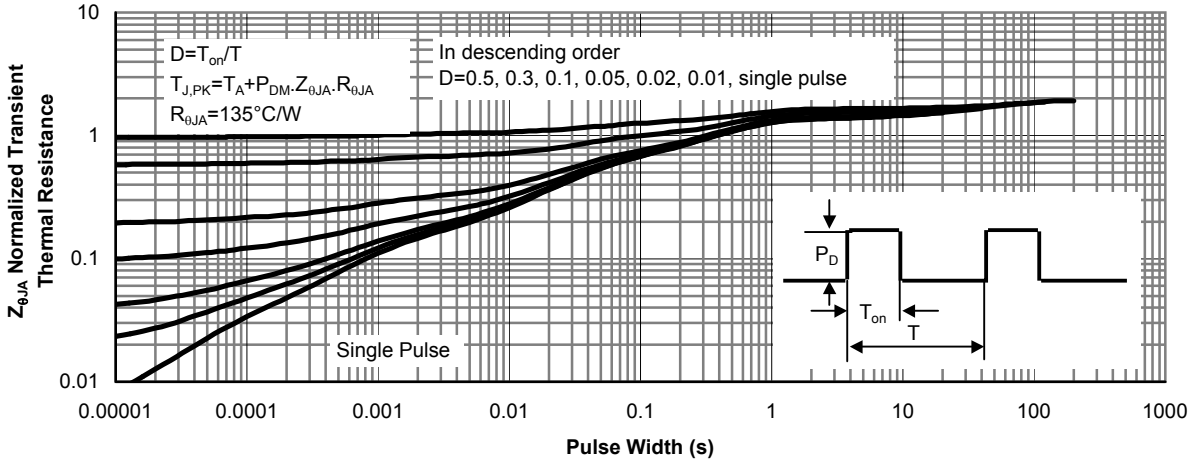


Figure 15: Schottky Normalized Maximum Transient Thermal Impedance